



ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089

## NTE2526 (NPN) & NTE2527 (PNP) Silicon Complementary Transistors High Current Switch

**Features:**

- Low Collector-Emitter Saturation Voltage
- High Current and High  $f_T$
- Excellent Linearity of  $h_{FE}$
- Fast Switching Time

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector Base Voltage, $V_{CBO}$ .....	120V
Collector Emitter Voltage, $V_{CEO}$ .....	100V
Emitter Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$	
Continuous .....	4A
Pulse .....	8A
Collector Power Dissipation, $P_C$	
$T_A = +25^\circ\text{C}$ .....	1W
$T_C = +25^\circ\text{C}$ .....	20W
Operating Junction Temperature, $T_J$ .....	$+150^\circ\text{C}$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+150^\circ\text{C}$

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 100\text{V}, I_E = 0$	-	-	1.0	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4\text{V}, I_C = 0$	-	-	1.0	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 5\text{V}, I_C = 500\text{mA}$	140	-	400	
		$V_{CE} = 5\text{V}, I_C = 3\text{A}$	40	-	-	
Gain-Bandwidth Product NTE2526	$f_T$	$V_{CE} = 10\text{V}, I_C = 500\text{mA}$	-	180	-	MHz
			-	130	-	MHz
Output Capacitance NTE2527	$C_{ob}$	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	-	40	-	pF
			-	65	-	pF

**Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage NTE2526	$V_{CE(sat)}$	$I_C = 2A, I_B = 200mA$	-	150	400	mV
NTE2527			-	200	500	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 2A, I_B = 200mA$	-	0.9	1.2	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	120	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	100	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	6	-	-	V
Turn-On Time	$t_{on}$	$V_{CC} = 50V, V_{BE} = -5V,$ $10I_{B1} = -10I_{B2} = I_C = 2A,$ Pulse Width = $20\mu s,$ Duty Cycle $\leq 1\%$ , Note 1	-	100	-	ns
Storage Time NTE2526	$t_{stg}$		-	900	-	ns
NTE2527			-	800	-	ns
Fall Time	$t_f$		-	50	-	ns

Note 1. For NTE2527, the polarity is reversed.

